

Vishay Semiconductors

Medium Power Silicon Rectifier Diodes, (Stud Version), 12 A



| PRIMARY CHARACTERISTICS | | | | |
|-------------------------|-----------------|--|--|--|
| I _{F(AV)} | 12 A | | | |
| Package | DO-4 (DO-203AA) | | | |
| Circuit configuration | Single | | | |

FEATURES

- Voltage ratings from 50 V to 1000 V
- · High surge capability



- Low thermal impedance
- High temperature rating
- Can be supplied as JAN and JAN-TX devices in accordance with MIL-S-19500/260
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

| MAJOR RATINGS AND CHARACTERISTICS | | | | |
|-----------------------------------|-----------------|-------------|------------------|--|
| PARAMETER | TEST CONDITIONS | VALUES | UNITS | |
| I _{F(AV)} | | 12 | A | |
| | T _C | 150 | °C | |
| I _{FSM} | 50 Hz | 230 | ^ | |
| | 60 Hz | 240 | Α | |
| I ² t | 50 Hz | 260 | A ² s | |
| | 60 Hz | 240 | A-5 | |
| T _J | | -65 to +200 | °C | |
| V _{RRM} | Range | 50 to 1000 | V | |

Note

ELECTRICAL SPECIFICATIONS

| VOLTAGE RA | VOLTAGE RATINGS | | | | |
|-------------|--|--|--|---|--|
| TYPE NUMBER | V _{RRM} , MAXIMUM REPETITIVE PEAK REVERSE VOLTAGE (T _C = -65 °C TO 200 °C) V | V _{R(RMS)} , MAXIMUM RMS REVERSE VOLTAGE (T _C = -65 °C TO 200 °C) V | V _{RSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE (T _C = -65 °C TO 200 °C) V | V _{RM} , MAXIMUM DIRECT REVERSE VOLTAGE (T _C = -65 °C TO 200 °C) V | |
| VS-1N1199A | 50 | 35 | 100 | 50 | |
| VS-1N1200A | 100 | 70 | 200 | 100 | |
| VS-1N1201A | 150 | 105 | 300 | 150 | |
| VS-1N1202A | 200 | 140 | 350 | 200 | |
| VS-1N1203A | 300 | 210 | 450 | 300 | |
| VS-1N1204A | 400 | 280 | 600 | 400 | |
| VS-1N1205A | 500 | 350 | 700 | 500 | |
| VS-1N1206A | 600 | 420 | 800 | 600 | |
| VS-1N3670A | 700 | 490 | 900 | 700 | |
| VS-1N3671A | 800 | 560 | 1000 | 800 | |
| VS-1N3672A | 900 | 630 | 1100 | 900 | |
| VS-1N3673A | 1000 | 700 | 1200 | 1000 | |
| VS-1N3624 | 1000 | 1200 | 1400 | 1000 | |

Notes

- JEDEC® registered values are in bold
- Basic part number indicates cathode to case; for anode to case, add "R" to part number, e.g., 1N1199RA

JEDEC® registered values are in bold



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| FORWARD COM | IDUCTION | | | | | |
|--|-------------------------------------|-----------------------------------|---|--|--------|------------------|
| PARAMETER | | SYMBOL | TEST CONDITIONS | | VALUES | UNITS |
| Maximum average forward current | | I _{F(AV)} | 180° sinusoidal conduction | | 12 | Α |
| at case temperature | at case temperature | | | | 150 | °C |
| | | | Half cycle 50 Hz sine wave or 6 ms rectangular pulse | Following any rated load condition and with rated V _{RRM} applied | 230 | - A |
| Maximum peak one cycle non-repetitive surge current | | I _{FSM} | Half cycle 60 Hz sine wave or 5 ms rectangular pulse | | 240 | |
| | | | Half cycle 50 Hz sine wave or 6 ms rectangular pulse | Following any rated load condition and with V _{RRM} applied following surge = 0 V | 275 | |
| | | | Half cycle 60 Hz sine wave or 5 ms rectangular pulse | | 285 | |
| | | | t = 10 ms | With rated V _{RRM} applied | 260 | |
| Maximum I ² t for fusin | Maximum I ² t for fusing | | t = 8.3 ms | following surge, initial T _J = 200 °C | 240 | A ² s |
| Maximum I ² t for individual device fusing | | _ l ² t | t = 10 ms | With $V_{RRM} = 0 \text{ V}$ following surge, initial $T_J = 200 \text{ °C}$ | 370 | |
| | | | t = 8.3 ms | | 340 | |
| Maximum l ² √t for individual device fusing | | I ² √t ⁽¹⁾ | t = 0.1 ms to 10 ms, V _{RRM} = 0 V following surge | | 3715 | A²√s |
| Maximum forward voltage drop | | V_{FM} | I _{F(AV)} = 12 A (38 A peak), T _C = 25 °C | | 1.35 | V |
| | V _{RRM} = 50 V | | Maximum rated I _{F(AV)} and T _C | | 3.0 | mA |
| | V _{RRM} = 100 V | | | | 2.5 | |
| | V _{RRM} = 150 V | | | | 2.25 | |
| | $V_{RRM} = 200 \text{ V}$ | I _{R(AV)} ⁽²⁾ | | | 2.0 | |
| | $V_{RRM} = 300 \text{ V}$ | | | | 1.75 | |
| Maximum average reverse current | V _{RRM} = 400 V | | | | 1.5 | |
| | $V_{RRM} = 500 \text{ V}$ | | | | 1.25 | |
| | $V_{RRM} = 600 \text{ V}$ | | | | 1.0 | |
| | $V_{RRM} = 700 \text{ V}$ | | | | 0.9 | |
| | $V_{RRM} = 800 \text{ V}$ | | | | 8.0 | |
| | V _{RRM} = 900 V | | | | 0.7 | |
| V _{RRM} = 1000 V | | | | | 0.6 | |

Notes

- JEDEC® registered values are in bold
- (1) I^2t for time $t_x = I^2\sqrt{t} \times \sqrt{t_x}$
- (2) Maximum peak reverse current (I_{RM}) under same conditions $\approx 2 \text{ x rated } I_{R(AV)}$

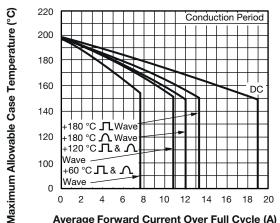
| THERMAL AND MECHANICAL SPECIFICATIONS | | | | | |
|---|---------|-----------------------------------|---|--------------|---------------------|
| PARAMETER | | SYMBOL | TEST CONDITIONS | VALUES | UNITS |
| Maximum operating case and storage temperature range | | T _C , T _{Stg} | | -65 to 200 | °C |
| Maximum internal thermal resistance, junction to case | | R_{thJC} | DC operation | 2.0 | °C 444 |
| Thermal resistance, case to sink | | R _{thCS} | Mounting surface, smooth, flat and greased | 0.5 | C/VV |
| | minimum | | Torque applied to nut; non-lubricated threads | 1.36 (12) | N · m (lbf · in) |
| | maximum | | Torque applied to flut, flori-lubricated tilleads | 1.69 (15) | |
| Mounting torque | minimum | | Taurus a serelia dita sereti lubricata dithuas da | 1.07 (9.45) | |
| Mounting torque | maximum | | Torque applied to nut; lubricated threads | 1.30 (11.55) | |
| | minimum | | Torque applied to device case; lubricated threads | 1.17 (10.35) | |
| | maximum | | | 1.43 (12.65) | |
| Approximate weight | | | | 7.0 | g |
| | | | | 0.25 | OZ. |
| Case style | | | JEDEC® DO-4 (DO-203/ | | D-203AA) |

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Average Forward Current Over Full Cycle (A)

Fig. 1 - Average Forward Current vs. Maximum Allowable Case Temperature

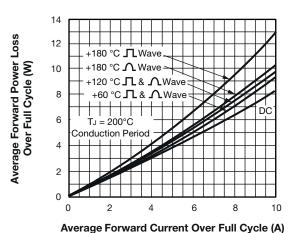
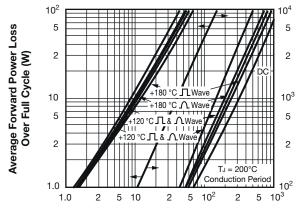
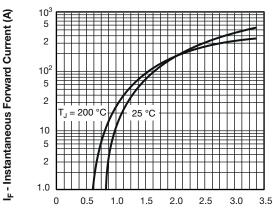


Fig. 2 - Maximum Low Level Forward Power Loss vs. Average Forward Current



Average Forward Current Over Full Cycle (A)

Fig. 3 - Maximum High Level Forward Power Loss vs. Average Forward Current



Instantaneous Forward Voltage (V)

Fig. 4 - Maximum Forward Voltage vs. Forward Current

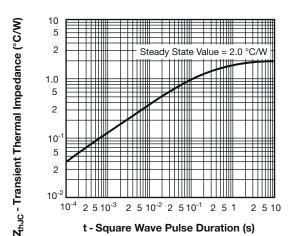
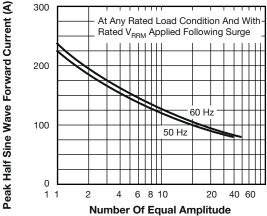


Fig. 5 - Maximum Transient Thermal Impedance, Junction to Case vs. Pulse Duration



Half Cycle Current Pulses (N)

Fig. 6 - Maximum Non-Repetitive 50 Hz Surge Current vs. **Number of Current Pulses**

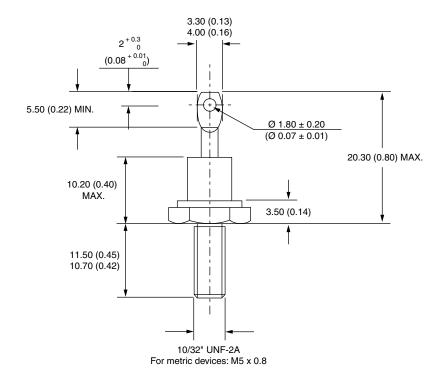
| LINKS TO RELATED DOCUMENTS | | |
|----------------------------|--------------------------|--|
| Dimensions | www.vishay.com/doc?95311 | |

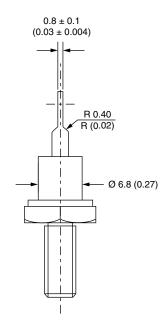


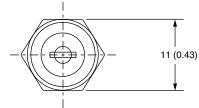
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DO-203AA (DO-4)

DIMENSIONS in millimeters (inches)









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